

In response to the Office Action dated June 25, 2001, Applicant respectfully requests entry of the Amendments set forth below and consideration of the remarks which follow:

IN THE SPECIFICATION

Please replace the paragraph on page 1, which starts at line 12, beginning with "Many devices are already known" as follows:

a1 Many devices are already known for depositing layers on substrates by so-called CVD (Chemical Vapor Deposition) or MOCVD (Metal Organic Chemical Vapor Deposition, i.e. when one or more precursors are present in the form of organometallic compounds) methods.

[IN THE] ABSTRACT

[Please insert the Abstract as follows on a separate sheet placed between page 19, the last page of the Description in the Specification, and page 20, the first page of the Claims.]

a2 The process for chemical vapor deposition of layers of material on a substrate which extend generally in a plane is disclosed. The process for depositing thin film materials on the substrate is made more economical by virtue of a better energy balance than previously disclosed. The substrate is heated by radiation from the heat of a duct but also by the gases passing over the substrate which themselves are heated by the duct. The heating of the gases further improves the coupling between the heating means and the substrate.